

S-Band Radar Transistor

The high power pulsed radar transistor part number IB2729M5 is designed for S-Band ATC radar systems operating over the instantaneous bandwidth of 2.7-2.9 GHz. While operating in class C mode this common base device supplies a minimum of 5 watts of peak pulse power under the conditions of 100µs pulse width and 10% duty cycle. All devices are 100% screened for large signal RF parameters, including power gain compression. Excellent spectral stability into output mismatch over a broad input power range make it ideal for use in reliable high power solid state transmitters.



Silicon Bipolar

- Ultra-high f_T

Class C Operation

- High Efficiency

Common Base Configuration

- Single Power Supply

Gold Metal

- Maximum Reliability

Emitter Ballasting

- Optimum Thermal Distribution

Internal Impedance Matching

- Ease of Use
- Ultra-low Loss Design

BeO Package

- Unmatched Thermal Reliability

RF Test Fixture

- Broadband
- Matched to 50Ω
- Long-term Correlation
- 100% Device RF Screening
- No External Tuning Allowed

Insertion Phase Marking

- N/A

US Patent Number

- 6181200B1
- 6331931B1

TYPICAL DATA TYPICAL DATA TYPICAL DATA TYPICAL DATA

Device	Freq (MHz)	V _{CC} (V)	P _{OUT} (W)	P _{IN} (W)	I _C (mA)	IRL (dB)	G _P (dB)	n _C (%)	Droop (dB)
D2610-4	2700	36	7	1.00	490	-9	8.3	39	-0.24
	2800	36	8	1.00	540	-21	9.3	44	-0.22
	2900	36	7	1.00	510	-22	8.5	39	-0.22

Pulse Format = 100µs, 10%

MAXIMUM RATINGS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Collector-Emitter Voltage	V_{CES}	--	65	V	$V_{BE}=0V$.
BD	Storage Temperature Range	T_{STG}	-55	+150	°C	--
BD	Operating Junction Temperature Range	T_J	-55	+200	°C	--
Note	Screen 'BD' = parameter qualified By Design.					

THERMAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
BD	Thermal Resistance	$R_{TH(JC)}$	--	3.5	°C/W	$V_{CC}=36V$, $PW=100\mu s$, $DF=10\%$, $T_F=25\pm 5^\circ C$, $P_{IN}=1W$
Note	Screen 'BD' = parameter qualified By Design.					

PROCESSING SPECIFICATIONS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	DC Wafer Probe	--	--	--	--	Per Integra specification
Q1	Wafer DC and RF Qualification	--	--	--	--	Per Integra specification
LM	Wire Bond Strength	--	--	--	--	Line monitor per Integra specification.
100%	Pre-cap visual inspection	--	--	--	--	Per Integra specification
100%	Gross leak test	--	--	--	--	MIL-STD-750D, Method 1071, Test Condition C
Note	Screen 'Q1' = parameter is qualified by assembly and test of 3 pieces minimum per wafer.					
Note	Screen 'LM' = parameter is qualified by assembly line monitor.					

DC ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Collector-Emitter Breakdown Voltage	BV_{CES}	65	--	V	$I_C=10mA$, $V_{BE}=0V$, $T_F=25\pm 5^\circ C$
100%	Zero Base Voltage Collector Leakage Current	I_{CES}	--	1.0	mA	$V_{CE}=30V$, $V_{BE}=0V$, $T_F=25\pm 5^\circ C$
100%	DC Current Gain	H_{FE}	10	100	--	$V_{CE}=5V$, $I_C=0.1A$, $T_F=25\pm 5^\circ C$

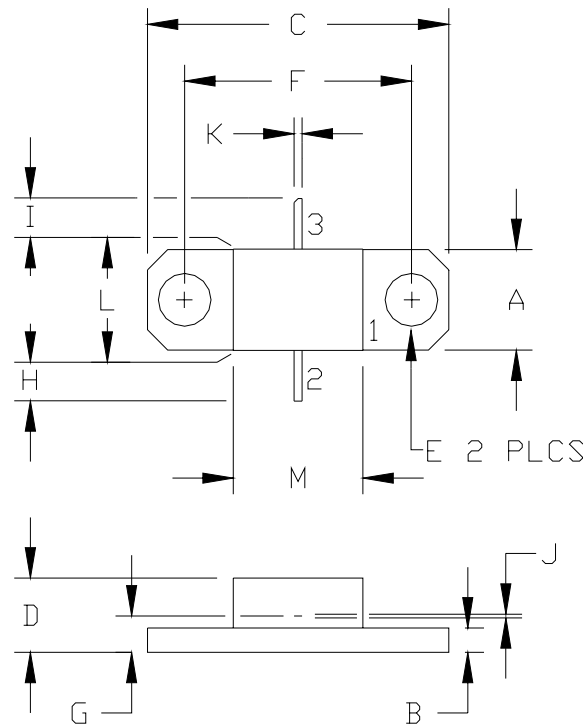
RF ELECTRICAL CHARACTERISTICS

Screen	Parameter	Symbol	Min	Max	Units	Test Conditions
100%	Input Return Loss	IRL	7	--	dB	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$
100%	Output Power	P_o	5	--	W	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$
100%	Collector Efficiency ($P_o/I_C/V_{CC}$)	N_C	30	--	%	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$
100%	Pulse Amplitude Droop	D	--	0.5	dB	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$
100%	Stability into 1.5:1 VSWR	VSWR-S	--	--	--	Rotate 1.5:1 output VSWR through 360° phase. No oscillatory or pulse break-up characteristics allowed on detected output pulse.
100%	2:1 Load Mismatch Tolerance	LMT	--	--	--	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$ Rotate 2:1 output VSWR through 360° phase, Survival.
BD	Pulse Risetime	RT	--	150	ns	$V_{CC}=36V, PW=100\mu s, DF=10\%, T_F=25\pm 5^\circ C, P_{IN}=1W, F=F1, F2, F3.$ Measure between 10% and 90% detected power points.
<p>Note 1 F1 = 2.70 GHz, F2 = 2.80 GHz, F3 = 2.90 GHz</p> <p>Note 2 Pulse format=100μs, 10%</p> <p>Note 3 T_F = Device flange temperature</p> <p>Note 4 Screen 'BD' = parameter qualified By Design</p>						

RF TEST FIXTURE IMPEDANCE CHARACTERISTICS

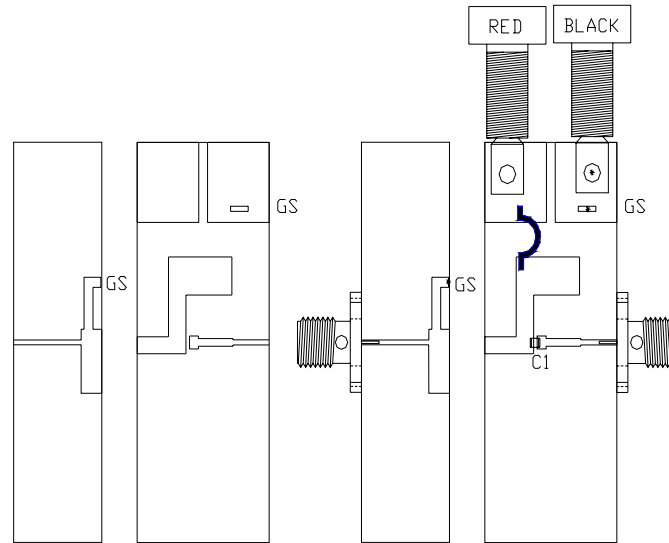
Frequency (MHz)	$Z_{IF} (\Omega)$	$Z_{OF} (\Omega)$
2.70	7.7 – j14.5	60.7 – j7.1
2.80	6.9 – j13.7	50.2 – j14.0
2.90	6.2 – j13.0	40.1 – j16.4
Impedance Definition		

PACKAGE DIMENSIONAL OUTLINE DRAWING



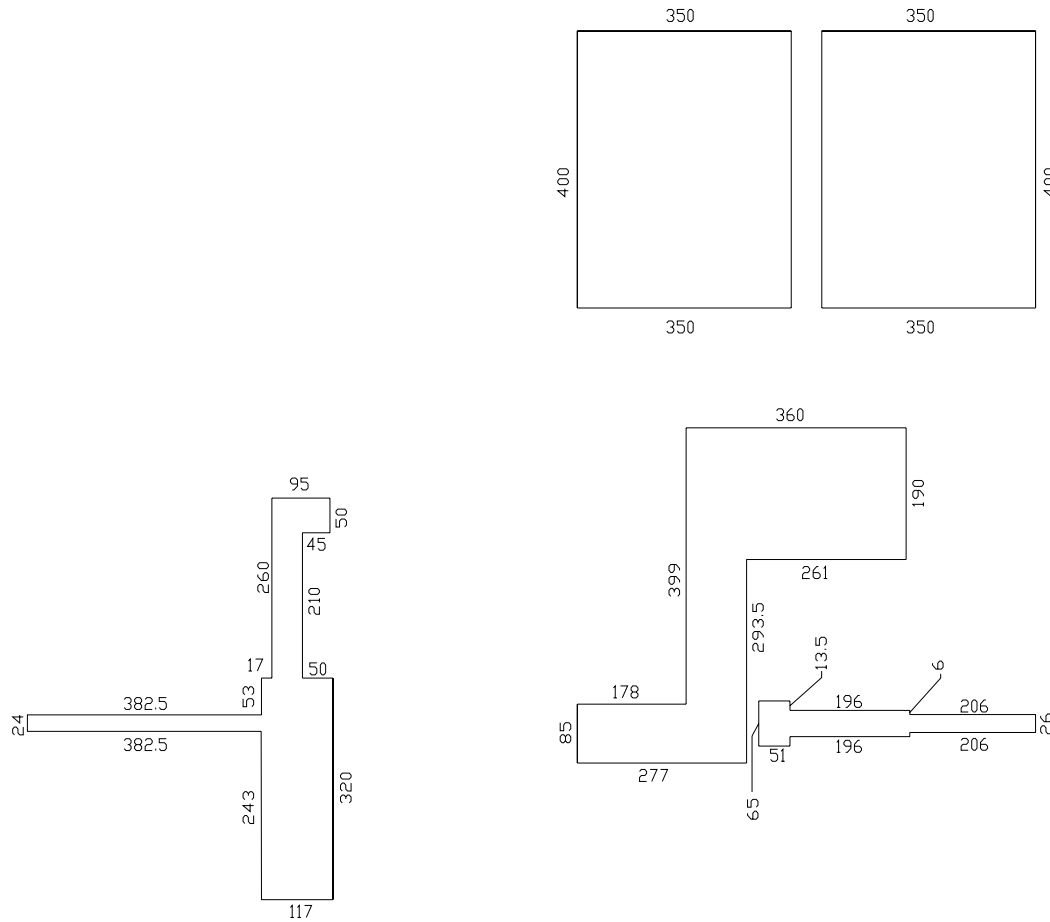
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.243	0.253	6.17	6.43
B	0.055	0.065	1.40	1.65
C	0.739	0.749	18.77	19.02
D	0.178	0.188	4.52	4.78
E	0.125	0.135	3.18	3.43
F	0.555	0.565	14.10	14.35
G	0.082	0.092	2.08	2.34
H	0.210	0.240	5.33	6.10
I	0.100	0.175	2.54	4.44
J	0.004	0.006	0.10	0.15
K	0.055	0.065	1.40	1.65
L	0.245	0.255	6.22	6.48
M	0.315	0.325	8.00	8.26

PIN SCHEDULE	
1	BASE
2	EMITTER
3	COLLECTOR

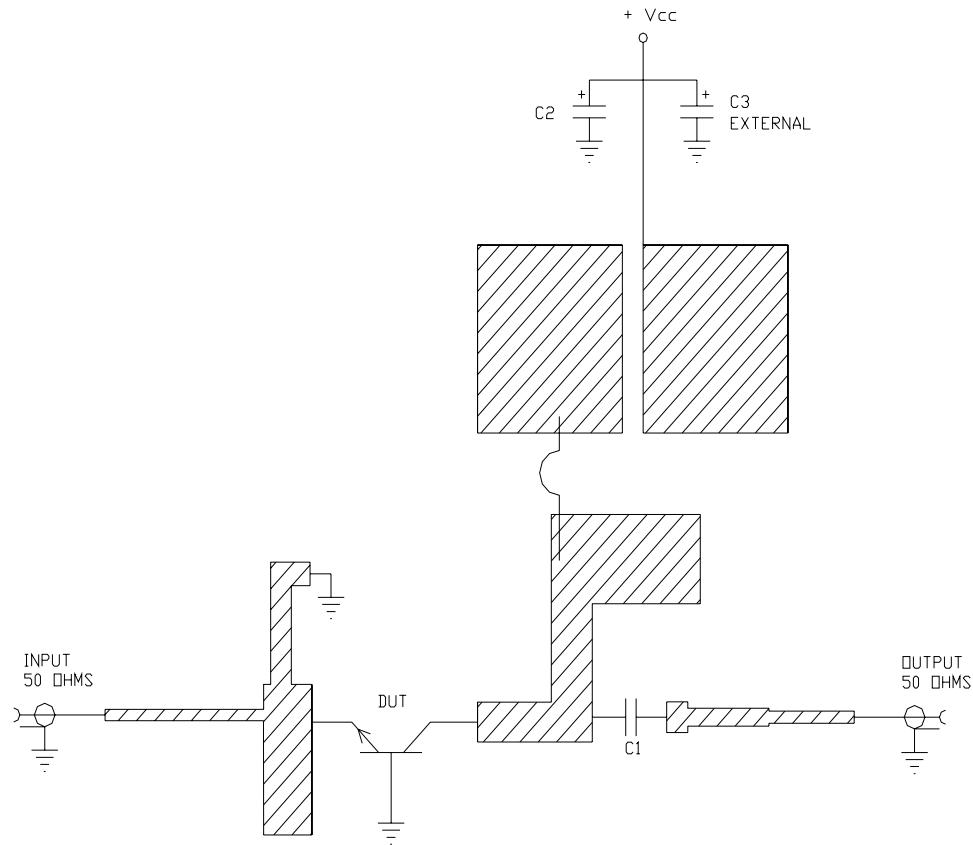


COMPONENT	DESCRIPTION
DUT	TRANSISTOR IB2729M5, MOUNT HARD TO THE RIGHT
PC BOARD	ROGERS #6010.2LM TH=0.025" 1E/1E
INPUT PC BOARD CARRIER	2 INCH BRASS -1 (0.50")
OUTPUT PC BOARD CARRIER	2 INCH BRASS -02 (0.75")
TRANSISTOR CARRIER	2 INCH COPPER -01
TRANSISTOR CLAMP	NDRYL CLAMP -01
HEATSINK	2 INCH HEATSINK -09
CONN1, CONN2	SMA CONNECTOR, TYPE DS #2052-5636-02
C1	CHIP CAPACITOR, TYPE ATC100A, 39pf
C2	ELECTROLYTIC CAPACITOR, 68uF / 63V
C3	ELECTROLYTIC CAPACITOR, 4700uF / 50V
DC CONN1	BANANA JACK, BLACK
DC CONN2	BANANA JACK, RED
GS	GROUND SHIM, COPPER, TH=0.001"
JW	JUMPER WIRE, COPPER, 0.22" DIA TYPICAL
NOTE	FIXTURE HARDWARE DRAWINGS AVAILABLE ON REQUEST

ASSEMBLY AND PARTS LIST



CIRCUIT DIMENSIONS



ELECTRICAL SCHEMATIC

DEFINITIONS

Data Sheet Status	
Proposed Specification	This data sheet contains proposed specifications.
Preliminary Specification	This data sheet contains specifications based on preliminary measurements and data.
Product Specification	This data sheet contains final product specifications.
Maximum Ratings	
Stress above one or more of the maximum ratings may cause permanent damage to the device. These are maximum ratings only and operation of the device at these or at any other conditions above those given in the characteristics sections of the specification is not implied. Exposure to maximum values for extended periods of time may affect device reliability.	

WARNING

Product and environmental safety - toxic materials
This product contains beryllium oxide. The product is entirely safe provided that the BeO base is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with general or domestic waste.

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